

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 10-189951

(43)Date of publication of application : 21.07.1998

(51)Int.CI.

H01L 29/78

(21)Application number : 08-348676

(71)Applicant : SANYO ELECTRIC CO LTD

(22)Date of filing : 26.12.1996

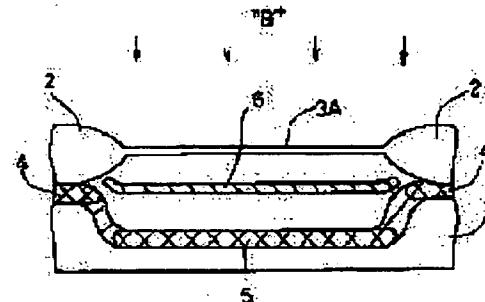
(72)Inventor : OKABE YUUSHIROU

(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To attain a high threshold voltage with low ion implantation, without causing degradation of isolation characteristic.

SOLUTION: Boron ions (11B+) are implanted under conditions for penetrating an LOCOS oxide 2 deposited on a P-type silicon substrate 1, in order to form a channel stopper layer 4 beneath the LOCOS oxide 2 of the same time as with a first channel ion implantation layer 5 in a deep region within the substrate 1. Subsequently, boron ions (11B+) are implanted from above the substrate 1 under conditions of not penetrating the LOCOS oxide 2, in order to form a second channel ion implantation layer 6 beneath a region for forming a diffusion layer in the substrate which is shallower than the first channel ion implantation layer 5.



LEGAL STATUS

[Date of request for examination] 22.02.2001

[Date of sending the examiner's decision of rejection] 03.12.2002

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

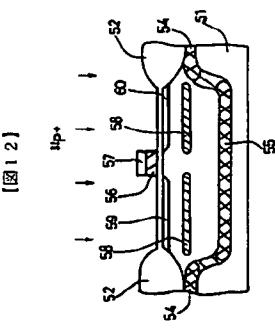
[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

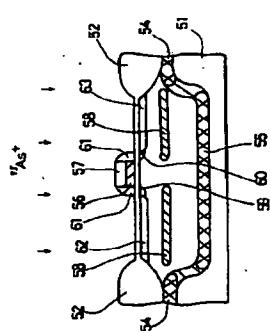
[Date of extinction of right]

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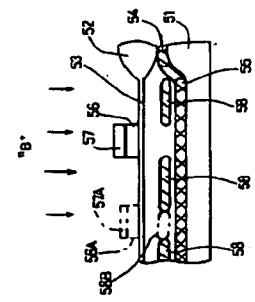
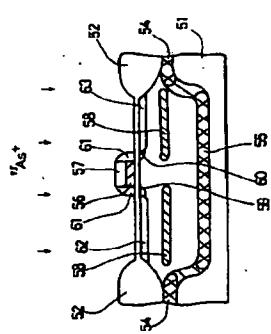


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